Shalini Lal

List of Publications by Year
in descending order

10 papers	82 citations	1937685 4 h-index	1872680 6 g-index
10 all docs	10 docs citations	10 times ranked	94 citing authors

#	Article	IF	Citations
1	Suppression of Anomalously Large Threshold Voltage in Wafer-Bonded Vertical Transistors by Enhancing Critical Field to Impact Ionization. IEEE Transactions on Electron Devices, 2018, 65, 1079-1086.	3.0	3
2	Barrier reduction via implementation of InGaN interlayer in wafer-bonded current aperture vertical electron transistors consisting of InGaAs channel and N-polar GaN drain. Applied Physics Letters, 2015, 106, .	3.3	4
3	Vertical electron transistors with In<inf>0.53</inf>Ga<inf>0.47</inf>As channel and N-polar In<inf>0.1</inf>Ga<inf>0.9</inf>N/GaN drain achieved by direct wafer-bonding. , 2014, , .		1
4	Engineering the (In, Al, Ga)N back-barrier to achieve high channel-conductivity for extremely scaled channel-thicknesses in N-polar GaN high-electron-mobility-transistors. Applied Physics Letters, 2014, 104, 092107.	3.3	26
5	Controlling electronic properties of wafer-bonded interfaces among dissimilar materials: A path to developing novel wafer-bonded devices. , 2013, , .		0
6	Controlling electronic properties of wafer-bonded interfaces among dissimilar materials: A path to developing novel wafer-bonded devices. , 2013, , .		1
7	Very high channel conductivity in ultra-thin channel N-polar GaN/(AlN, InAlN, AlGaN) high electron mobility hetero-junctions grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2013, 102, 232104.	3.3	19
8	Wafer-Bonded p-n Heterojunction of GaAs and Chemomechanically Polished N-Polar GaN. IEEE Electron Device Letters, 2013, 34, 42-44.	3.9	18
9	Experimental demonstration of a wafer-bonded heterostructure based unipolar transistor with In<inf>0.53</inf>Ga<inf>0.47</inf>as channel and III-N drain. , 2012, , .		0
10	InGaAs-InGaN Wafer-Bonded Current Aperture Vertical Electron Transistors (BAVETs). Journal of Electronic Materials, 2012, 41, 857-864.	2.2	10